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# 2SB1404

Silicon PNP Triple Diffused

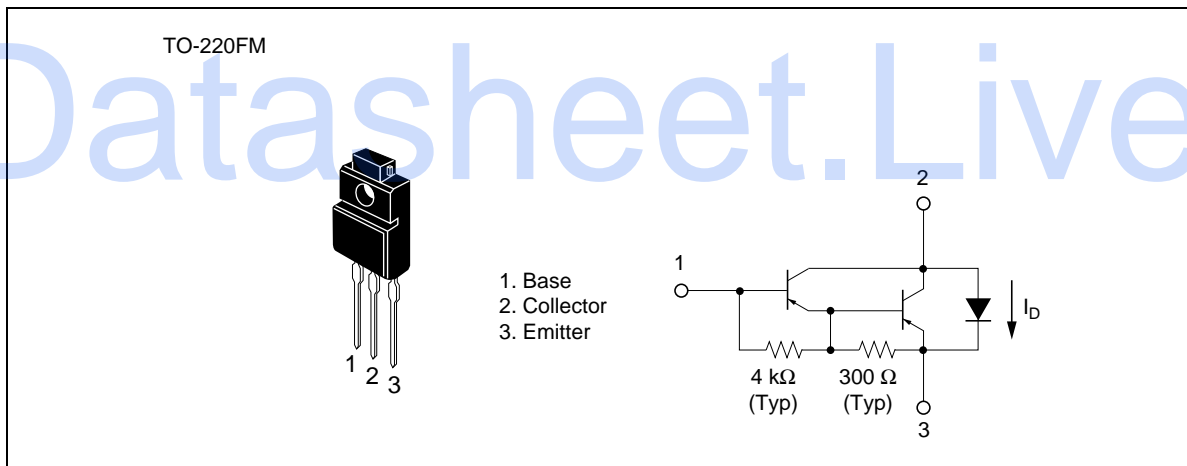
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### Application

Low frequency power amplifier

### Outline



## 2SB1404

### Absolute Maximum Ratings (Ta = 25°C)

| Item                         | Symbol        | Ratings     | Unit |
|------------------------------|---------------|-------------|------|
| Collector to base voltage    | $V_{CBO}$     | -120        | V    |
| Collector to emitter voltage | $V_{CEO}$     | -120        | V    |
| Emitter to base voltage      | $V_{EBO}$     | -7          | V    |
| Collector current            | $I_C$         | -3          | A    |
| Collector peak current       | $I_{C(peak)}$ | -6          | A    |
| Collector power dissipation  | $P_C$         | 2           | W    |
|                              | $P_C^{*1}$    | 25          |      |
| Junction temperature         | $T_j$         | 150         | °C   |
| Storage temperature          | $T_{stg}$     | -55 to +150 | °C   |

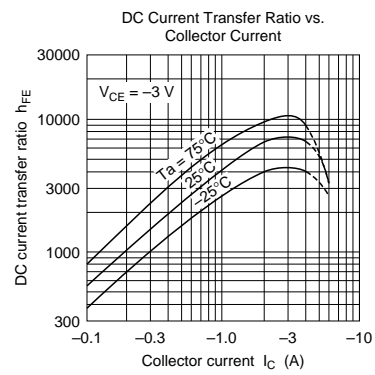
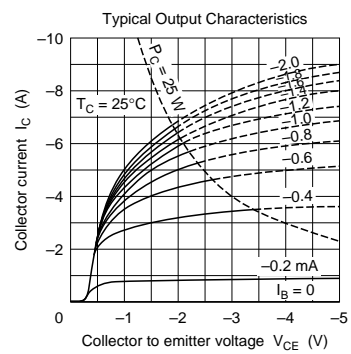
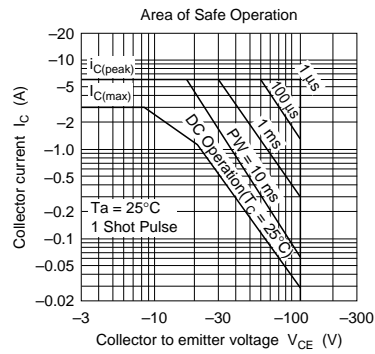
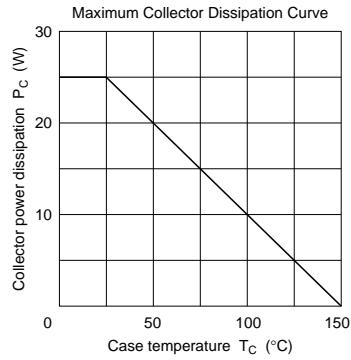
Note: 1. Value at  $T_C = 25^\circ\text{C}$ .

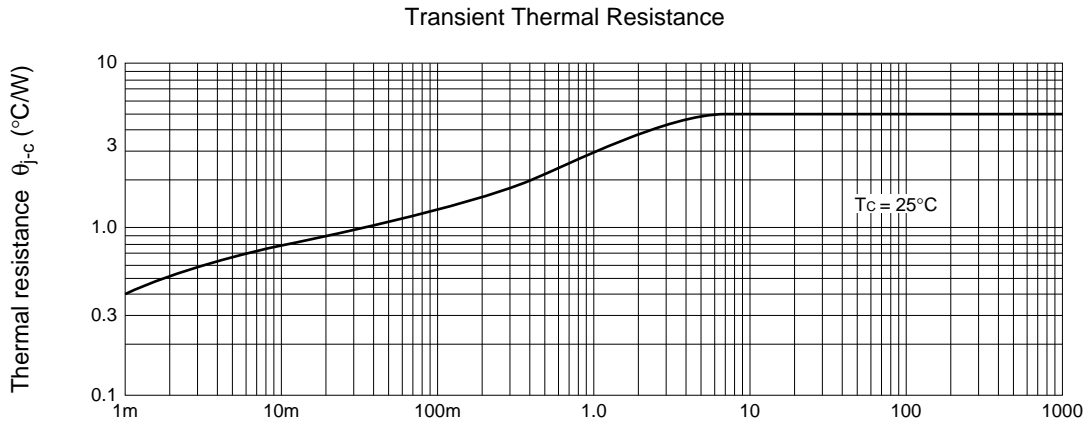
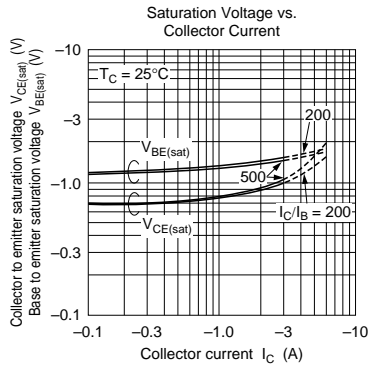
### Electrical Characteristics (Ta = 25°C)

| Item                                    | Symbol         | Min  | Typ | Max   | Unit          | Test conditions                                     |
|---|----------------|------|-----|-------|---------------|---|
| Collector to base breakdown voltage     | $V_{(BR)CBO}$  | -120 | —   | —     | V             | $I_C = -0.1\text{ mA}$ , $I_E = 0$                  |
| Collector to emitter breakdown voltage  | $V_{(BR)CEO}$  | -120 | —   | —     | V             | $I_C = -25\text{ mA}$ , $R_{BE} = \infty$           |
| Emitter to base breakdown voltage       | $V_{(BR)EBO}$  | -7   | —   | —     | V             | $I_E = -50\text{ mA}$ , $I_C = 0$                   |
| Collector cutoff current                | $I_{CBO}$      | —    | —   | -10   | $\mu\text{A}$ | $V_{CB} = -100\text{ V}$ , $I_E = 0$                |
|   | $I_{CEO}$      | —    | —   | -10   |               | $V_{CE} = -100\text{ V}$ , $R_{BE} = \infty$        |
| DC current transfer ratio               | $h_{FE}$       | 1000 | —   | 20000 |               | $V_{CE} = -3\text{ V}$ , $I_C = -1.5\text{ A}^{*1}$ |
| Collector to emitter saturation voltage | $V_{CE(sat)1}$ | —    | —   | -1.5  | V             | $I_C = -1.5\text{ A}$ , $I_B = -3\text{ mA}^{*1}$   |
|   | $V_{CE(sat)2}$ | —    | —   | -3.0  |               | $I_C = -3\text{ A}$ , $I_B = -30\text{ mA}^{*1}$    |
| Base to emitter saturation voltage      | $V_{BE(sat)1}$ | —    | —   | -2.0  | V             | $I_C = -1.5\text{ A}$ , $I_B = -3\text{ mA}^{*1}$   |
|   | $V_{BE(sat)2}$ | —    | —   | -3.5  |               | $I_C = -3\text{ A}$ , $I_B = -30\text{ mA}^{*1}$    |

Note: 1. Pulse test.

See switching characteristic curve of 2SB765(K).





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# HITACHI

**Hitachi, Ltd.**

Semiconductor & IC Div.  
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan  
Tel: Tokyo (03) 3270-2111  
Fax: (03) 3270-5109

**For further information write to:**

Hitachi America, Ltd.  
Semiconductor & IC Div.  
2000 Sierra Point Parkway  
Brisbane, CA. 94005-1835  
U S A  
Tel: 415-589-8300  
Fax: 415-583-4207

Hitachi Europe GmbH  
Electronic Components Group  
Continental Europe  
Dornacher Straße 3  
D-85622 Feldkirchen  
München  
Tel: 089-9 91 80-0  
Fax: 089-9 29 30 00

Hitachi Europe Ltd.  
Electronic Components Div.  
Northern Europe Headquarters  
Whitebrook Park  
Lower Cookham Road  
Maidenhead  
Berkshire SL6 8YA  
United Kingdom  
Tel: 0628-585000  
Fax: 0628-778322

Hitachi Asia Pte. Ltd.  
16 Collyer Quay #20-00  
Hitachi Tower  
Singapore 0104  
Tel: 535-2100  
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.  
Unit 706, North Tower,  
World Finance Centre,  
Harbour City, Canton Road  
Tsim Sha Tsui, Kowloon  
Hong Kong  
Tel: 27359218  
Fax: 27306071